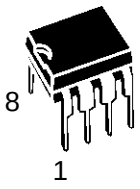
SGS-THOMSON MICROELECTRONICS

ST93C06
ST93C06C

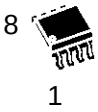
SERIAL MICROWIRE BUS 256 bit (16 x 16 or 32 x 8) EEPROM

DATA BRIEFING

- 1 MILLION ERASE/WRITE CYCLES, with 40 YEARS DATA RETENTION
- DUAL ORGANIZATION: 16 x 16 or 32 x 8
- BYTE/WORD and ENTIRE MEMORY PROGRAMMING INSTRUCTIONS
- SELF-TIMED PROGRAMMING CYCLE with AUTO-ERASE
- READY/BUSY SIGNAL DURING PROGRAMMING
- SINGLE 5V ±10% SUPPLY VOLTAGE
- SEQUENTIAL READ OPERATION
- 5ms TYPICAL PROGRAMMING TIME
- ENHANCED ESD/LATCH UP PERFORMANCES for "C" VERSION

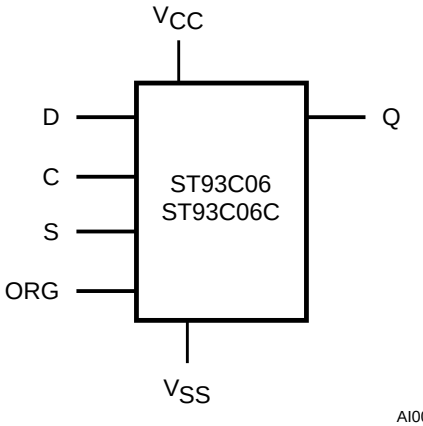


PSDIP8 (B)
0.4mm Frame



SO8 (M)
150mil Width

Logic Diagram



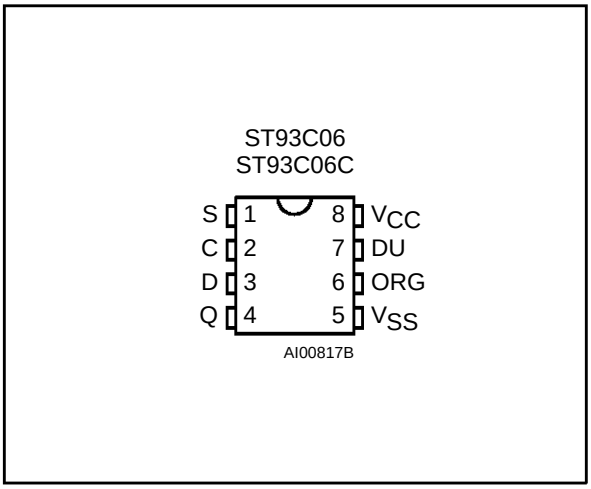
DESCRIPTION

The ST93C06 and ST93C06C are 256 bit Electrically Erasable Programmable Memory (EEPROM) fabricated with SGS-THOMSON's High Endurance Single Polysilicon CMOS technology. In the text the two products are referred to as ST93C06.

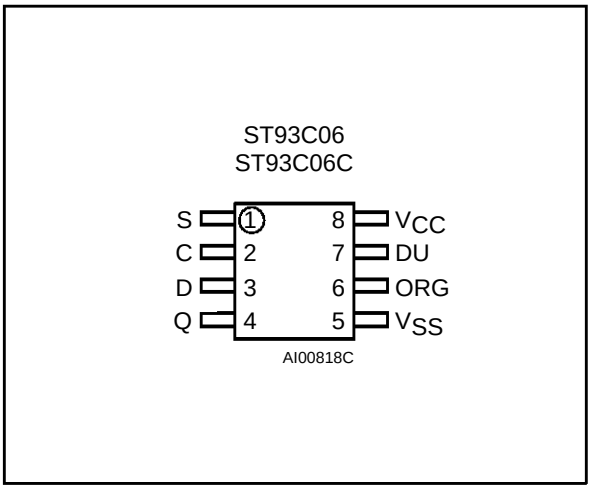
The memory is divided into either 32 x 8 bit bytes or 16 x 16 bit words. The organization may be selected by a signal applied on the ORG input.

The memory is accessed through a serial input (D) and by a set of instructions which includes Read a byte/word, Write a byte/word, Erase a byte/word, Erase All and Write All. A Read instruction loads the address of the first byte/word to be read into an internal address pointer.

DIP Pin Connections



SO Pin Connections



Signal Names

S	Chip Select Input
D	Serial Data Input
Q	Serial Data Output
C	Serial Clock
ORG	Organisation Select
V_{CC}	Supply Voltage
V_{SS}	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.
For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: ST93C06C M 1 013TR

Revision
- blank CMOS F3 Tech.
- C CMOS F4 Tech.

Package
- B PSDIP8 0.4mm Frame
- M SO8 150mil Width

Temp. Range
- 1 0 to 70 °C
- 6 –40 to 85 °C
- 3 –40 to 125 °C

Option
- 013TR Tape & Reel Packing